

## CORRECTION

[View Article Online](#)  
[View Journal](#) | [View Issue](#)

Cite this: *J. Mater. Chem. C*, 2025, **13**, 8336

DOI: 10.1039/d5tc90053k

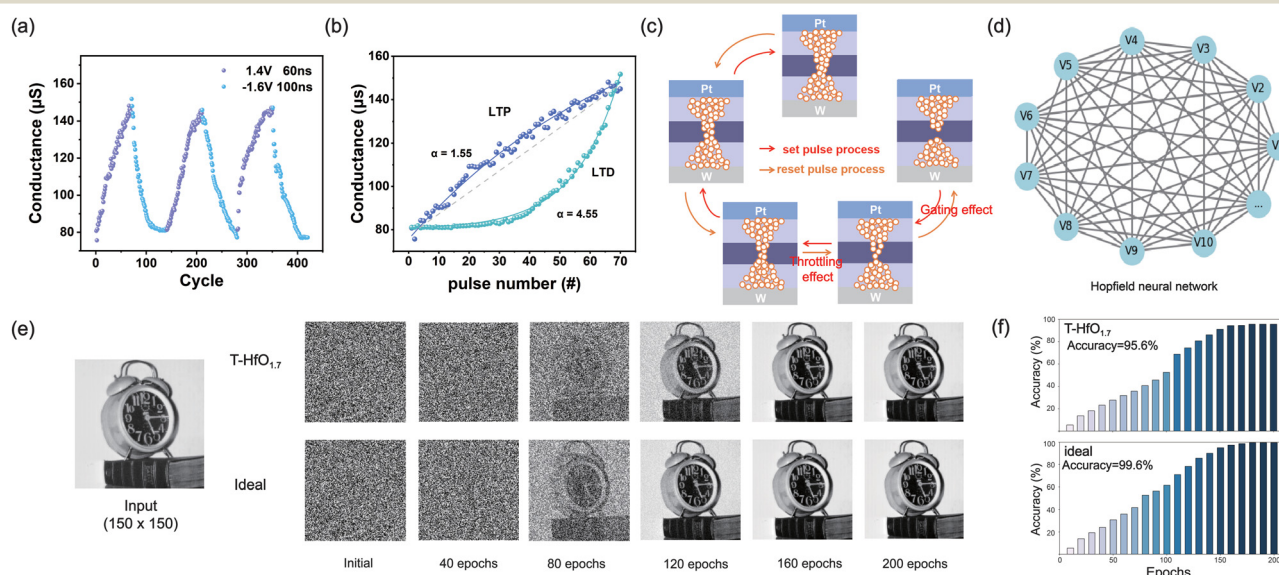
[rsc.li/materials-c](https://rsc.li/materials-c)

## Correction: An ion-gating synaptic memristor based on tri-layer $\text{HfO}_x$ composition regulation

Lanqing Zou,<sup>a</sup> Junming Zhang,<sup>a</sup> Yunhui Yi,<sup>a</sup> Jiawang Ren,<sup>a</sup> Huajun Sun,<sup>\*ab</sup> Chuqian Zhu,<sup>a</sup> Jiyang Xu,<sup>a</sup> Sheng Hu,<sup>ac</sup> Lei Ye,<sup>ab</sup> Weiming Cheng,<sup>ab</sup> Qiang He<sup>ab</sup> and Xiangshui Miao<sup>ab</sup>

Correction for 'An ion-gating synaptic memristor based on tri-layer  $\text{HfO}_x$  composition regulation' by Lanqing Zou *et al.*, *J. Mater. Chem. C*, 2025, **13**, 5326–5331, <https://doi.org/10.1039/D4TC04564E>.

The authors regret that an incorrect version of Fig. 4a was included in the published article, showing incorrect data points for the first cycle. This does not impact any of the conclusions of the article. The corrected version of Fig. 4 is shown in this notice.



**Fig. 4** (a) Cycle-to-cycle conductance evolution. (b) LTP/LTD process linearity fitting graph. (c)  $V_O$  migration diagram in the CFs during LTP/LTD. (d) Structure of the HNN. (e) Alarm clock images display process during 200 weight updates in HNN learning with the T- $\text{HfO}_{1.7}$  and the device with ideal linearity. (f) The learning accuracy for the HNN.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup> School of Integrated Circuits, Hubei Key Laboratory of Advanced Memories, Hubei Engineering Research Center on Microelectronics, Huazhong University of Science and Technology, Wuhan 430074, China. E-mail: [shj@hust.edu.cn](mailto:shj@hust.edu.cn)

<sup>b</sup> Hubei Yangtze Memory Laboratories, Wuhan 430205, China

<sup>c</sup> Wuhan Xinxin Semiconductor Manufacturing Corporation, Wuhan, 430205, China